

## **Description**

The HXY3401I-ED usesadvancedtrenchtechnologytoprovide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.



**SOT-23** 

#### **General Features**

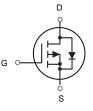
 $V_{DS} = -20V, I_{D} = -3A$ 

 $R_{DS(ON)} < 130 \text{m} \Omega @ V_{GS} = -4.5 \text{V}$ 

 $R_{DS(ON)}$  < 148m  $\Omega$  @  $V_{GS}$ =-2.5V

## **Application**

PWM applications Load switch



P-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
HXY3401I-ED	SOT-23	A19T	3000

### Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	-20	V
V <sub>G</sub> s	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current-Continuous	-3	А
Ідм	Drain Current-Pulsed (Note 1)	-10	А
P <sub>D</sub>	Maximum Power Dissipation	0.7	W
T <sub>J</sub> ,T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 To 150	°C
Rеja	Thermal Resistance,Junction-to-Ambient (Note 2)	178	°C/W



## Electrical Characteristics (T<sub>A</sub>=25 ℃ unless otherwise noted)

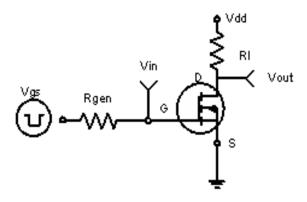
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-20		-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-0.4	-0.7	-1	V
Drain-Source On-State Resistance		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A		100	130	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1.8A		132	148	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-2A	4	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =-10V,V <sub>GS</sub> =0V, F=1.0MHz	-	285	-	PF
Output Capacitance	C <sub>oss</sub>		-	58	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	r-1.0ivinz	-	32	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	9.8	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =-10V, $R_L$ =5 $\Omega$	-	4.9	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GS}}$ =-4.5 $V$ , $R_{\text{GEN}}$ =3 $\Omega$	-	20.5	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =-10V,I <sub>D</sub> =-2A, V <sub>GS</sub> =-4.5V	-	2.9	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	0.45	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V GS4.0 V	-	0.75	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-2A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-2.0	Α

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

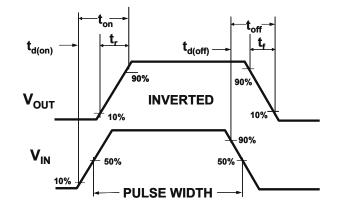
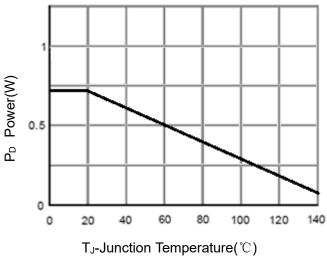
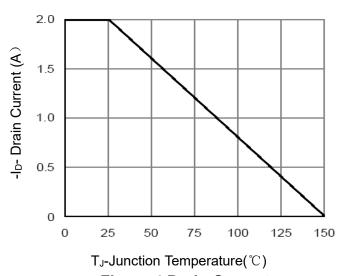


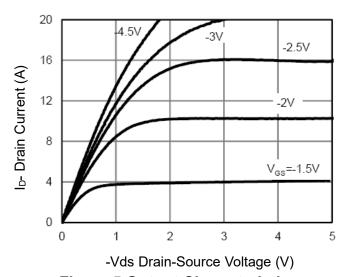
Figure 2:Switching Waveforms



**Figure 3 Power Dissipation** 



**Figure 4 Drain Current** 



**Figure 5 Output Characteristics** 

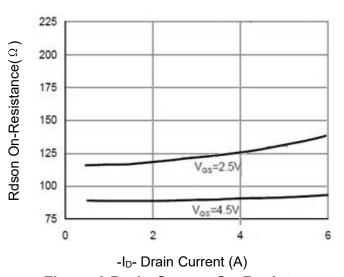
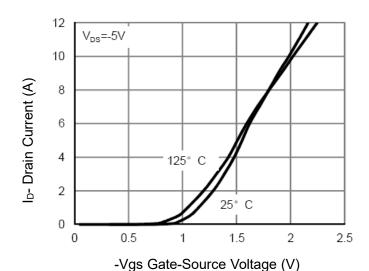


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 

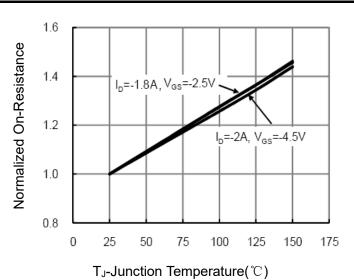


Figure 8 Drain-Source On-Resistance

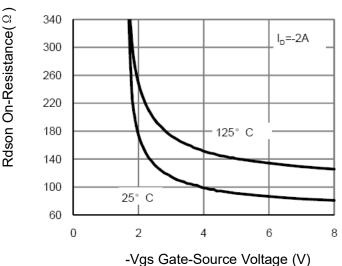


Figure 9 Rdson vs Vgs

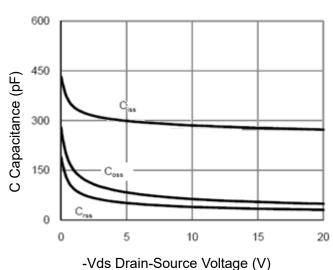


Figure 10 Capacitance vs Vds

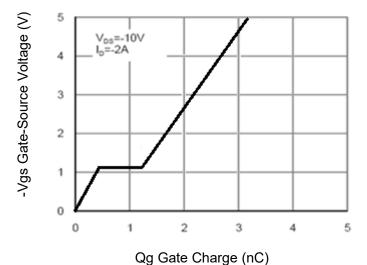


Figure 11 Gate Charge

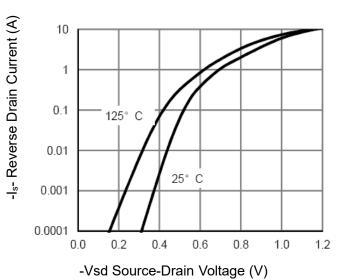


Figure 12 Source- Drain Diode Forward



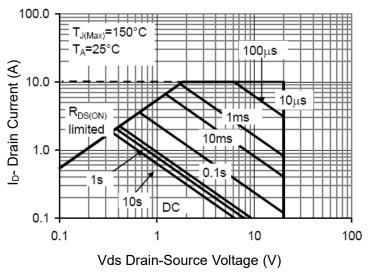
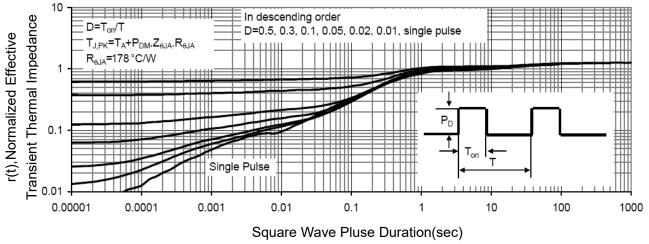


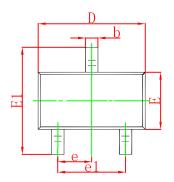
Figure 13 Safe Operation Area

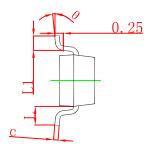


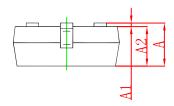
**Figure 14 Normalized Maximum Transient Thermal Impedance** 

# P-Channel Enhancement Mode MOSFET

## **SOT-23 Package Outline Dimensions**

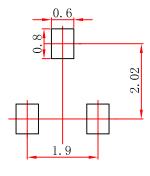






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## **SOT-23 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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